

IP5 Rec'd PCT/PTO 28 SEP 2006

Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 28953.2004	Application No. 10/594,846 New - unassigned
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Makoto Iwai et al	10/594846 Group Art Unit 1792
		Filing Date 11/08/2006 Herewith	

U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
/F.H./	AA	6,949,140	9/2005	Sarayama et al	117	81	
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Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publn. Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
/F.H./	AC	2002-293696	10/2002	Japan			Abstract	
/F.H./	AD	2003-292400	10/2003	Japan			Abstract	
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/F.H./	AG	WO2004/013385	6/2003	WIPO			Abstract	
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Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
/F.H./	AP	Kawamura, F. et al, "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique," Jpn. J. Appl. Phys., Vol. 42 (2003), pp. L4-L6
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	AT	

Examiner Signature /Felisa Hiteshew/	Date Considered 04/11/2008
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Disclosure Form (PTO-1449)

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./